

REMARKS

Reconsideration and allowance of this application, as amended, are requested. This amendment is being filed concurrently with a Request for Continued Examination.

Applicant respectfully disagrees with some of the Examiner's characterizations set forth in the office action of May 2, 2003. In particular the Examiner stated:

"In Ma et al, region 89 is still located beneath the metallization 133 since region 89 is on top of the substrate and the metallization 133 transcends the substrate. Regarding whether the metallization 133 are signal input pads, this is shown by the flat regions on the top of metallization 133. The metallization serve as electrodes to the gate 55 are clearly used to send signals to the gate of the MOSFET. Regarding the new language "beneath" and "above" in claims 1, 7 and 18, 19, this new language clarifies the claims and would overcome the 112 rejection."

In Applicant's view, the Examiner still does not appreciate certain differences between the claimed inventions and the teachings of the Ma reference, even though they have been previously explained.

A significant feature of the claimed inventions is that a low resistance layer having broad area is disposed directly under (or beneath) the signal input pad. This low resistance layer functions as a shield. This positional relationship refers to the relation between the input pad 116 and the impurity high-concentration diffused region 106 as illustrated in Figs. 1 and 2.

The Examiner states that the metallization regions 133 are signal input pads. In Applicant's view, the Examiner misunderstands Ma's structure. The structure in Ma's Fig. 8 only shows main features of Ma's invention. On the illustrated structure, an interlayer insulating film (like the insulating film 113 of our inventions) should be deposited. Therefore, the metallization regions 133, etc. are not exposed and these regions cannot be signal input

pads. Signal input pads mean, for example, portions where wires are bonded, or testing probes are contacted.

In contrast, our input pad 116 is exposed. Therefore, metallization region 133 of Ma and input pad 116 of our claimed inventions have completely different structures and functions.

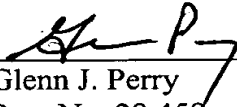
In Ma's structure, the corresponding element 89 is not located beneath the element 133 as shown in Fig. 8.

Accordingly, in Ma et al., there is neither disclosed nor suggested that a low resistance layer should be disposed just under the signal input pad. Furthermore, there is no description of a signal input pad and its shape and location. Therefore, Ma et al. do not disclose such essential features of our claims.

All outstanding matters having been addressed, it is respectfully submitted that the present application is in a condition for allowance and a Notice to that effect is earnestly solicited.

Respectfully submitted,

By: _____


Glenn J. Perry
Reg. No. 28,458
Telephone: (703) 905-2161
Direct Fax: (703) 738-2277

PILLSBURY WINTHROP LLP
1600 Tysons Boulevard
McLean, Virginia 22102
Switchboard: (703) 905-2000
Office fax: 703-905-2500